



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Thomas A. Figura, Kevin Donohoe, & Thomas Dunbar

Serial No.: 09/471,460

Filed: December 22, 1999

Title: USE OF A PLASMA SOURCE TO FORM A LAYER
DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

§ Group Art Unit: 2825
§ Application Examiner: Calvin Lee
§ Atty. Docket: 94-0280.03
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H. J. / Jennifer C.
C. C. / Carol
6/6/01

AMENDMENT AND RESPONSE TO THE
OFFICE ACTION DATED NOVEMBER 21, 2000

Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Certificate of Mailing	
I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to:	
Commissioner for Patents Washington, DC 20231	
Date: 5-31-01	Signature

Applicants submit this Amendment and Response to the Office Action dated November 21, 2000. Please amend the accompanying continued prosecution application as follows.

IN THE CLAIMS

Please cancel claims 20-22 without prejudice.

Please amend the claims to the following form.

① 44. (Once amended) A method of providing a polymer between metal features on a wafer, comprising:

C 1 performing a deposition on said wafer in a site; and
etching in the same general site used to perform said deposition.

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